RECTIFIER DIODES (BRIDGE TYPE) (Ta=25°C)

Parts No.	Maximum ratings				Electrical characteristics			Fig. No.	Remarks
	V_{RM} (V)	Io (A)	I_{FSM} (A)	Tstg (°C)	V_F (V) max	V_F Condition I_F(A)	I_R (μA) max		
RB-150	50	1.5	40	−40~+140	0.95	1.0	10	16	
-151	100								
-152	200								
-154	400								
-156	600								
-158	800								
LB-156	600	1.5	120	−40~+140	0.91	1.0	10	16	
RBA-401	100	4.0‡	80	−40~+150	1.05	2.0	10	17	
-402	200								
RBV-404	400	4.0‡	60	−40~+150	1.10	2.0	10	18	
-406	600								
-408	800		100		1.0				
-406M	600		120		0.92				
-406H					1.0				
RBV-601	100	6.0‡	120	−40~+150	1.00	3.0	10	19	
-602	200								
-604	400		100		1.05				
-606	600								
-608	800		170		0.95				
RBV-1506	600	15‡	200	−40~+150	1.05	7.5	50	19	
-2506		25‡	350			12.5			

‡With fin

HIGH VOLTAGE RECTIFIER DIODES (Ta=25°C)

Parts No.	Maximum ratings					Electrical characteristics				Fig. No.
	V_{RM} (kV)	Io (mA)	I_{FSM} (A)	Tc (°C)	Tstg (°C)	V_F (V) max	V_F Condition I_F(mA)	I_R (μA) max	trr (μs) max	
SHV-02	2	2.0	0.3	—	−40~+120	16	10	1.0	0.18	20
SHV-03	3		0.5	100		16				21
-06	6					26				23
-08	8					36				
-10	10					40				24
-12	12					45				
-14	14					55				25
-16	16					60				
-20	20					75				
-24	24					75				
SHV-06NK	6	2.0	0.5	100	−40~+120	26	10	1.0	0.18	22
-08NK	8					36				
-10K	10					40				24
-12K	12					45				
-06UNK	6					48			0.15	22
-08UNK	8					60				
-10UK	10					60				24
-12UK	12					68				
-16UK	16					90				25
-08X	8					60				24
-08XN	8					55				22

MICROWAVE OVEN DIODES (Ta=25°C)

Parts No.	Maximum ratings				Electrical characteristics			Fig. No.
	V_{RM} (kV)	Io (mA)	I_{FSM} (A)	Tstg (°C)	V_F (V) max	V_F Condition I_F(mA)	I_R (μA) max	
HVR-1X-40B	9	350	20	−40~+130	9	350	10	26
UX-FOB	8	350	15	−30~+130	16	350	10	27

HIGH SPEED RECTIFIER DIODES (Ta=25°C)

Parts No.	Maximum ratings				Electrical characteristics				Fig. No.
	V_{RM} (V)	Io (A)	I_{FSM} (A)	Tstg (°C)	V_F (V) max	V_F Condition I_F(A)	I_R (μA) max	trr (μs)	
RC 2	2000	0.2	20	−40~+130	2.0	0.2	10	4.0	
RU 1	400	0.25	15	−40~+130	2.5	0.25	10	0.4	3
1A	600								
1B	800								
1C	1000	0.2			3.0				
EU 1Z	200	0.25	15	−40~+140	2.5	0.25	10	0.4	4
1	400								
1A	600								
EU01Z	200	0.25*	15	−40~+140	2.5	0.25	10	0.4	5
01	400								
01A	600								
EP01C	1000	0.2	5	−40~+140	4.0	0.2	5	0.2	5
EH 1Z	200	0.6	30	−40~+140	1.35	0.6	10	4.0	4
1	400								
1A	600								
RF 1Z	200	0.6	15	−40~+130	2.0	0.6	10	0.4	3
1	400								
1A	600								
1B	800								
RH 1Z	200	0.6	35	−40~+130	1.3	0.6	5	4.0	3
1	400								
1A	600								
1B	800								
1C	1000								
AS01Z	200	0.6	20	−40~+150	1.50	0.6	10	1.5	2
01	400								
01A	600								
AP01C	1000	0.2	5	−40~+150	4.0	0.2	100	0.2	2
ES01Z	200	0.7*	30	−40~+140	2.5	0.8	10	1.5	5
01	400								
01A	600								
01F	1500	0.5*	20		2.0	0.5			
ES 1Z	200	0.7	30	−40~+140	2.5	0.8	10	1.5	4
1	400								
1A	600								
1F	1500	0.5	20		2.0	0.5			
RS 1A	600	0.7	30	−40~+130	2.5	0.8	10	1.5	3
1B	800								
RH 2F	1500	1.0	60	−40~+130	1.0	1.0	10	4.2	6
AU01Z	200	0.5	15	−40~+150	1.70	0.5	10	0.4	2
01	400								
01A	600								
AU02Z	200	0.8	25	−40~+150	1.30	0.8	10	0.4	2
02	400								
02A	600								
EP01C	1000	0.2	5	−40~+140	4.0	0.2	5	0.2	5
RU 2Z	200	1.0	20	−40~+130	1.5	1.0	10	0.4	3
2	600								
2B	800								

*With print substrate

AVALANCHE DIODES

(Ta=25°C)

Parts No.	Maximum ratings			Electrical characteristics			Fig. No.
	V_{RM} (V)	I_{ZSM} (A) Momentary	T_{stg} (°C)	V_Z (V) 1mA Momentary	I_R (μA)	$I_{R(H)}$ (μA)	
RM 25	40	3.0	−40~+130	50~61.5	5	20	3
RM 26	50			60~70			
R 2M	130	1.0	−40~+150	135~180	10	50	3
RY 23	200	0.1	−40~+130	250~400	10	50	3
RY 24	400			400~450			

POWER ZENER DIODES

(Ta=25°C)

Parts No.	Maximum ratings				Electrical characteristics			Remarks	Fig. No.
	P_R (W)	V_{DC} (V)	V_{ZSM}(A) Momentary	T_{stg} (°C)	V_Z (V) 1mA Momentary	I_R (mA)	$H \cdot I_R$ (mA)		
PZ127	150	20	4	−40~+150	27±5	0.5	1.0		3
227	300		8						6
427	450		9						8
628	1500		40						34

GaAs SCHOTTKY BARRIER DIODES(GSC SERIES)

Maximum ratings

(Ta=25°C)

Parts No.	V_{RM} (V)	Io (A) Rectangular wave duty 1/2 average	Tc (°C)	I_{FSM}*(A) 50Hz half sine wave peak value	I^2t*(A^2s) 50Hz half sine wave Single shot	Tj(°C)	Tstg(°C)
GSC215	150	5	114	20	2.0	−40~ +150	−40~ +150
GSC218	180						
GSC235	350	2	115	8	0.3		
GSC315	150	14	80	50	18		
GSC318	180						

* Per element

Electrical and thermal characteristics

(Ta=25°C)

Parts No.	V_F* (V)	I_F (A)	I_R*(mA) $V_R=V_{RM}$ max	$I_{R(H)}$*(mA) $V_R=V_{RM}$max Tj=150°C	trr*(ns) dif/dt=100A/μs	I_F (A)	Co*(pF) $V_R=0^V$ f_M=1MHz	$R_{th(j-c)}$(°C/W)	Fig. No.
GSC215	0.90	2.5	1.0	10	7	2	150	5.0	13
GSC218				15					
GSC235	1.50	1.0		4.5	5	1	100		
GSC315	0.90	7.0	3.0	30	10	6	450	3.5	14
GSC318				45					

* Per element

Full view (Unit: mm)

Fig. 1

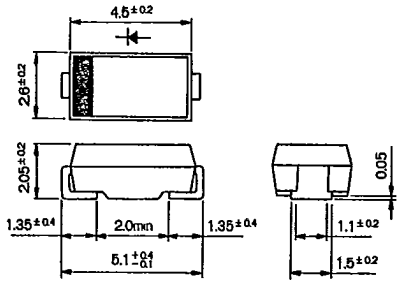


Fig. 2

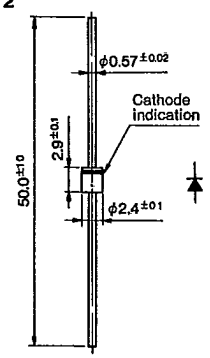


Fig. 3

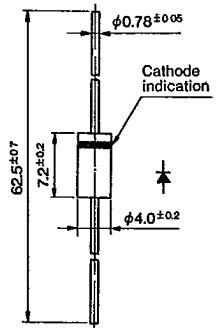
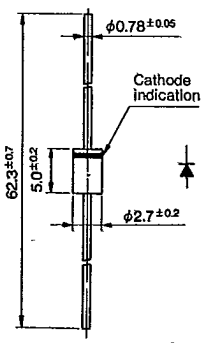


Fig. 4



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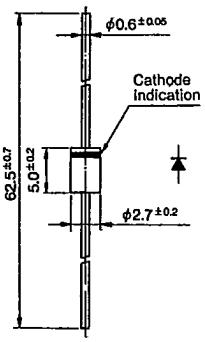

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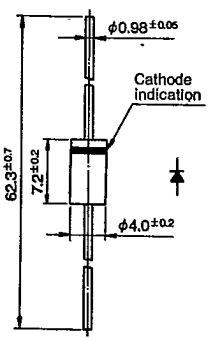


Fig. 7

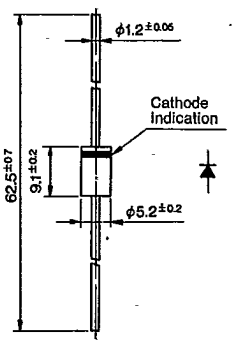


Fig. 8

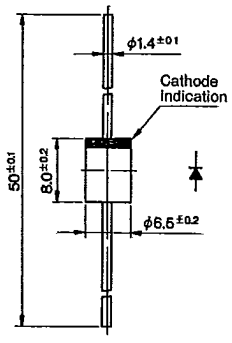


Fig. 9

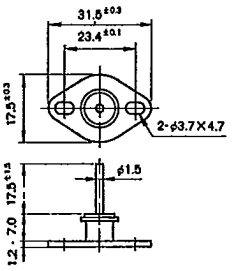


Fig. 10

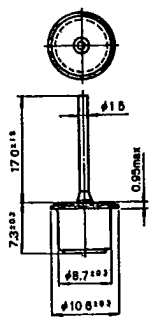


Fig. 11

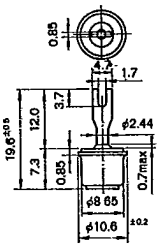


Fig. 12

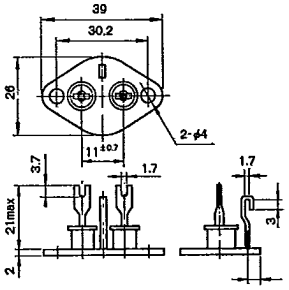


Fig. 13 (TO-220)

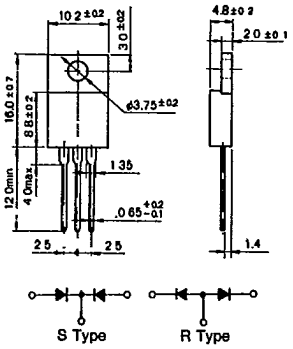


Fig. 14 (TO-3P)

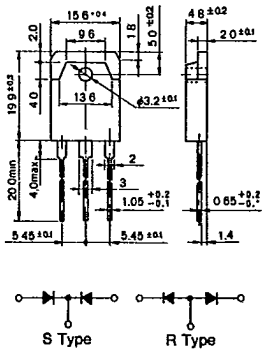


Fig. 15

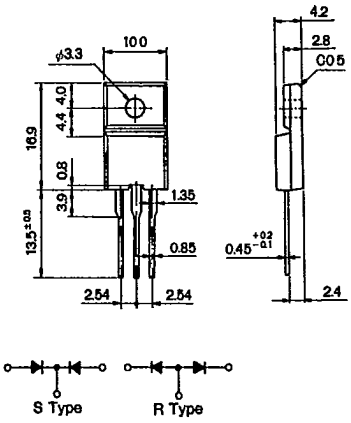
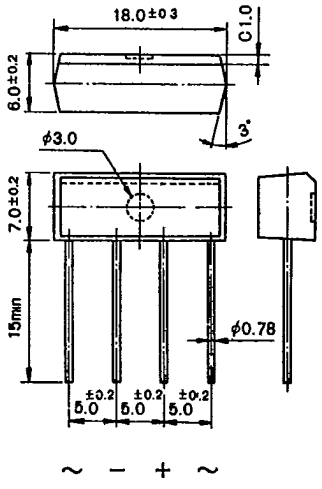


Fig. 16



T-91-20

Fig. 17

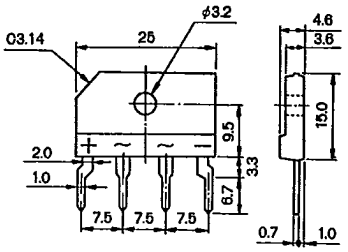


Fig. 18

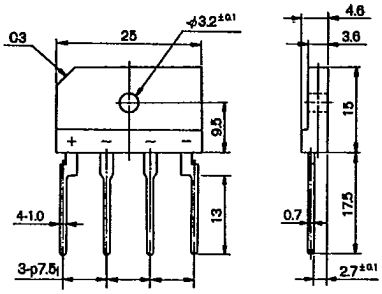


Fig. 19

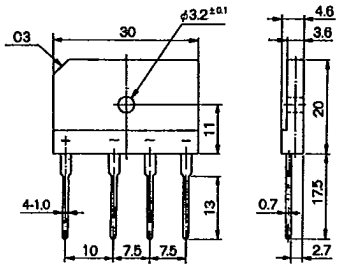


Fig. 20

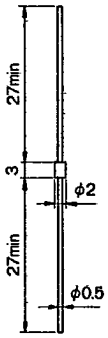


Fig. 21

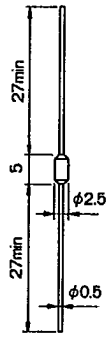


Fig. 22

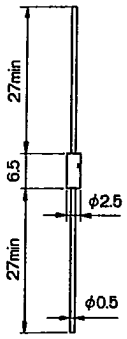


Fig. 23

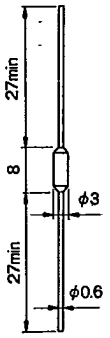


Fig. 24

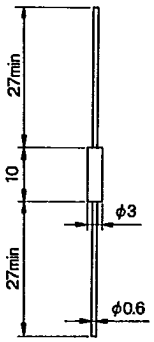


Fig. 25

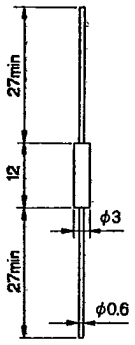


Fig. 26

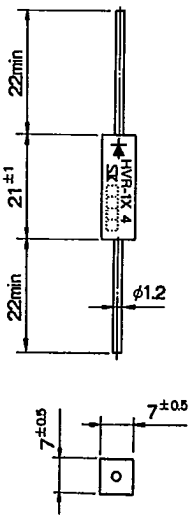


Fig. 27

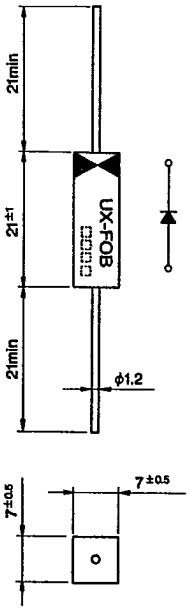


Fig. 28